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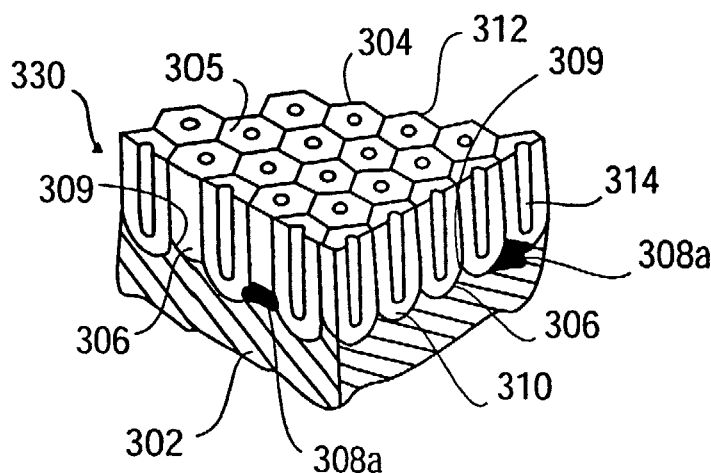
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(57) Abstract: We have discovered that the formation of particulate inclusions at the surface of an aluminum alloy article, which inclusions interfere with a smooth transition from the alloy surface to an overlying aluminum oxide protective film can be controlled by maintaining the content of mobile impurities and compounds thereof; by heat-treating the aluminum alloy at a temperature less than about 330 °C ; and by creating the aluminum oxide protective film by employing a particular electrolytic process. When these factors are taken into consideration, an improved aluminum oxide protective film is obtained.

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